

## EXERCISE SERIES 6

### Exercise 1: Absorption

- a) Which thickness of material do you need to absorb 90 % of the light with  $\lambda = 500 \text{ nm}$  and  $1000 \text{ nm}$  in amorphous Si and in crystalline Si. Absorption coefficients are given in Tab. 1

Table 1: Absorption coefficients

$\lambda[\text{nm}]$	$\alpha$ for a-Si:H [ $\text{cm}^{-1}$ ]	$\alpha$ for c-Si [ $\text{cm}^{-1}$ ]
500	$2 \cdot 10^5$	$10^4$
1000	0.9	80

- b) Draw the absorption profile for an intensity  $F_0$  in a semi infinite wafer with a reflection of 10 % with  $\lambda = 500 \text{ nm}$  and  $1000 \text{ nm}$  in amorphous Si and in crystalline Si.
- c) Taking the results of a) & b) into account, what are options to increase the absorption to more than 99% in the films without making them thicker than what you calculated in a) ?

### Exercise 2: Antireflection layer

Consider a multilayer stack with refractive indices  $n_1$ ,  $n_2$ , and  $n_3$ . The Fresnel equation of reflection at normal incidence for two layers  $i$  and  $j$  is  $r_{ij} = ((n_i - n_j)/(n_i + n_j))^2$ . To achieve minimal reflection the second reflection  $r_{23}$ , should nullify  $r_{21}$ . Derive a condition linking  $n_1$ ,  $n_2$ , and  $n_3$ .